

# Freeform Search

Database:	US Palents Full-Text Database US Pre-Grant Publication Full-Text Database JPO Abstracts Database EPO Abstracts Database Derwent World Patents Index IBM Technical Disclosure Bulletins
Term: Display: Generate:	Documents in Display Format: TI Starting with Number 1
Generate:	Hit List  ● Hit Count  ○ Image  Search

### Search History

Freeform Search

I of 2

http://westbrs:8820/bin/gate.exe?state=sgp52b.27.1&t=ffsearch&format=KWIC

<b>DB</b> Name	Query	Hit Count	Set Name
USPT	111 and 115	6	<u>L16</u>
USPT	13 and 19 and 113	6	<u>L15</u>
USPT	112 and 113	6	<u>L14</u>
USPT	('4117063'  '4937284'  '4333898'  '4058583'  '4289860'  '5112919')[PN]	6	<u>L13</u>
USPT	110 and 111	43	<u>L12</u>
USPT	extruder or extruded or extruding	136448	<u>L11</u>
USPT	18 and 19	2	<u>L10</u>
USPT	granulate or granules or granulated or granulating	100528	<u>L9</u>
USPT	16 and 17	313	<u>L8</u>
USPT	ldpe or polyethylene or ethylene polymer	265323	<u>L7</u>
USPT	13 and 15	564	<u>L6</u>
USPT	14.ab.	4146	<u>L5</u>
USPT	silane or trimethoxysiane or vinyltrimethoxysilane	45646	<u>L4</u>
USPT	cable or wire	558171	<u>L3</u>

L1	FILE	'CAPLUS' ENTERED AT 18:24:11 ON 10 JAN 2002 1 S JP04293945/PN
L2 L3	FILE	'DPCI' ENTERED AT 18:27:42 ON 10 JAN 2002 1 S JP04293945/PN OR WO0036612/PN 2 S JP04293945/PN OR WO200036612/PN SEL PN.G
L4	FILE	'CAPLUS' ENTERED AT 18:28:42 ON 10 JAN 2002 1 S E1/PN
L5	FILE	'DPCI' ENTERED AT 18:32:25 ON 10 JAN 2002 1 S US4289860/PN SEL PN.G
L6 L7 L8	FILE	'CAPLUS' ENTERED AT 18:33:05 ON 10 JAN 2002 0 S L2-E12/PN 7 S E2-E12/PN 7 S L7 NOT L4
=>		

```
ANSWER 1 OF 1 CAPLUS COPYRIGHT 2002 ACS
AN
     1998:561362 CAPLUS
DN
     129:169066
TI
     Semiconductive resin composition, its preparation, and a power cable using
IN
     Yoshida, Yoshie; Mizutani, Toshikazu; Kitaqawa, Masaki; Deguchi, Jichio
PA
     Mitsubishi Chemical Corp., Japan
SO
     Eur. Pat. Appl., 17 pp.
     CODEN: EPXXDW
DT
     Patent
LΑ
     English
ΙC
     ICM H01B001-24
     76-2 (Electric Phenomena)
CC
     Section cross-reference(s): 38
FAN.CNT 1
                     KIND DATE
     PATENT NO.
                                          APPLICATION NO.
                                                           DATE
                     ____
     -----
                                          -----
                                                           _____
     EP 858081
                     A2
                           19980812
PΙ
                                         EP 1998-102132
                                                           19980206
     EP 858081
                     A3 19990203
       R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,
            IE, SI, LT, LV, FI, RO
     JP 10279769
                     A2
                          19981020
                                          JP 1998-24254
                                                           19980205
     CA 2228925
                      AA 19980807
                                          CA 1998-2228925
                                                           19980206
                     Α
     US 5985181
                           19991116
                                          US 1998-20897
                                                           19980209 <--
PRAI JP 1997-24972
                           19970207
     There is provided a semiconductive resin compn. comprising: (A) 5-100
     parts by wt. of a modified ethylene copolymer obtainable by subjecting an
     ethylene copolymer and a vinyl monomer to graft polymn. conditions; (B)
     0.5-15 parts by wt. of an unsatd. silane compd.; (D) 10-110 parts by wt.
     of C black; and (E) 0-95 parts by wt. of an ethylene copolymer, based on
     100 parts by wt. total of (A) and (E); the component (B) is incorporated
     into the compn. by subjecting the component (B) to melt graft reaction
     together with the component (A) and/or component (E) in the presence of
     0.01-2 parts by wt. of a radical generator (C); the vinyl monomer unit is
     contained in an amt. of 5-35\% by wt. of the total amt. of the components
     (A) and (E); and the degree of crosslinking of the compn. is 30-90% by wt.
ST
     semiconductive resin compn prodn use; power cable semiconductive resin
IT
     Carbon black, uses
     RL: TEM (Technical or engineered material use); USES (Uses)
       (Vulcan XC72 and Denka Black; in prepn. of semiconductive resin compn.
       for power cables)
ΙT
     Crosslinking
     Graft polymerization
        (in prepn. of semiconductive resin compn. for power cables)
ΙT
     Silanes
    RL: RCT (Reactant); TEM (Technical or engineered material use); USES
        (in prepn. of semiconductive resin compn. for power cables)
IT
    Electric cables
        (power; prepn. of semiconductive resin compn. for)
ΙT
    Semiconductor materials
        (prepn. of semiconductive resin compn. for power cables)
IT
    Polymers, uses
    RL: DEV (Device component use); PNU (Preparation, unclassified); TEM
     (Technical or engineered material use); PREP (Preparation); USES (Uses)
        (prepn. of semiconductive resin compn. for power cables)
    9003-53-6P, Polystyrene 9010-86-0P, Ethylene-ethyl acrylate copolymer
IT
    24937-78-8P, Ethylene-vinyl acetate copolymer 35312-82-4P,
    Ethylene-vinyltrimethoxysilane copolymer
    RL; DEV (Device component use); PNU (Preparation, unclassified); TEM
     (Technical or engineered material use); PREP (Preparation); USES (Uses)
```

(prepn. of semiconductive resin compn. for power cables contq.)

```
ANSWER 1 OF 1 CAPLUS COPYRIGHT 2002 ACS
     1998:561362 CAPLUS
AN
DN
     129:169066
     Semiconductive resin composition, its preparation, and a power cable using
TΙ
IN
     Yoshida, Yoshie; Mizutani, Toshikazu; Kitagawa, Masaki; Deguchi, Jichio
PA
     Mitsubishi Chemical Corp., Japan
     Eur. Pat. Appl., 17 pp.
SO
     CODEN: EPXXDW
DT
     Patent
LA
     English
IC
     ICM H01B001-24
CC
     76-2 (Electric Phenomena)
     Section cross-reference(s): 38
FAN.CNT 1
     PATENT NO.
                     KIND DATE
                                          APPLICATION NO. DATE
     _____
                     ----
                                          -----
                                                           _____
     EP 858081
                    A2 19980812
ΡI
                                         EP 1998-102132
                                                          19980206
     EP 858081
                     A3 19990203
         R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,
             IE, SI, LT, LV, FI, RO
     JP 10279769
                     A2
                          19981020
                                          JP 1998-24254
                                                           19980205
     CA 2228925
                      AA 19980807
                                          CA 1998-2228925
                                                           19980206
     US 5985181
                     Α
                           19991116
                                         US 1998-20897
                                                           19980209 <--
PRAI JP 1997-24972
                           19970207
     There is provided a semiconductive resin compn. comprising: (A) 5-100
     parts by wt. of a modified ethylene copolymer obtainable by subjecting an
     ethylene copolymer and a vinyl monomer to graft polymn. conditions; (B)
     0.5-15 parts by wt. of an unsatd. silane compd.; (D) 10-110 parts by wt.
     of, C black; and (E) 0-95 parts by wt. of an ethylene copolymer, based on
     100 parts by wt. total of (A) and (E); the component (B) is incorporated
     into the compn. by subjecting the component (B) to melt graft reaction
     together with the component (A) and/or component (E) in the presence of
     0.01-2 parts by wt. of a radical generator (C); the vinyl monomer unit is
     contained in an amt. of 5-35\% by wt. of the total amt. of the components
     (A) and (E); and the degree of crosslinking of the compn. is 30-90% by wt.
ST
     semiconductive resin compn prodn use; power cable semiconductive resin
IT
     Carbon black, uses
     RL: TEM (Technical or engineered material use); USES (Uses)
        (Vulcan XC72 and Denka Black; in prepn. of semiconductive resin compn.
        for power cables)
IT
     Crosslinking
     Graft polymerization
        (in prepn. of semiconductive resin compn. for power cables)
IT
     Silanes
    RL: RCT (Reactant); TEM (Technical or engineered material use); USES
     (Uses)
        (in prepn. of semiconductive resin compn. for power cables)
TT
    Electric cables
       , (power; prepn. of semiconductive resin compn. for)
IT
    Semiconductor materials
        (prepn. of semiconductive resin compn. for power cables)
TT
    Polymers, uses
    RL: DEV (Device component use); PNU (Preparation, unclassified); TEM
     (Technical or engineered material use); PREP (Preparation); USES (Uses)
        (prepn. of semiconductive resin compn. for power cables)
    9003-53-6P, Polystyrene 9010-86-0P, Ethylene-ethyl acrylate copolymer
IT
    24937-78-8P, Ethylene-vinyl acetate copolymer 35312-82-4P,
    Ethylene-vinyltrimethoxysilane copolymer
    RL: DEV (Device component use); PNU (Preparation, unclassified); TEM
     (Technical or engineered material use); PREP (Preparation); USES (Uses)
```

(prepn. of semiconductive resin compn. for power cables contg.)

```
L1
     ANSWER 1 OF 1 CAPLUS COPYRIGHT 2002 ACS
ΑN
     1993:104471 CAPLUS
DN
     118:104471
TI
     Silane-crosslinked resin semiconductive compositions for cable covering
IN
     Nishiyama, Hidemi; Kimura, Hitoshi
     Furukawa Electric Co., Ltd., Japan
PA
SO
     Jpn. Kokai Tokkyo Koho, 11 pp.
     CODEN: JKXXAF
DT
     Patent
LΑ
     Japanese
IC
     ICM C08L023-08
     ICS C08K003-04; C08K005-14; C08K005-54; C08K005-56; H01B001-24
     38-3 (Plastics Fabrication and Uses)
     Section cross-reference(s): 76
FAN.CNT 1
     PAŤENT NO.
                    KIND DATE
                                          APPLICATION NO. DATE
     _____
                     ----
                                           ______
PΤ
     JP 04293945 A2
                           19921019
                                          JP 1991-60448
                                                          19910325 <--
AΒ
     The title compns comprise ethylene (I) polymers 60-95, .gtoreq.1 I
     copolymers with vinyl acetate, propylene, Et acrylate (II), Me acrylate,
     and/or acrylic acid 5-40, elec. conductive carbon 15-80, org. silanes
     0.5-10.0, org. peroxides 0.05-5.0, and silanol condensation catalysts
     0.01-3.0 parts. Thus, a 5.7-mm-diam. twisted wire was covered with a
     compn. contg. LLDPE 80, I-II copolymer 20, elec. conductive carbon 60,
     vinyltrimethoxysilane 2.0, dicumyl peroxide 0.2, dibutyltin dilaurate 0.1,
     and Irganox 1010 0.3 part and crosslinked in water at 80.degree. for 24 h
     to form a 1.0-mm semiconductive layer showing elongation 350% and good
     surface smoothness.
ST
     silane crosslinking ethylene polymer semiconductor
ΙT
     Semiconductor materials
     Plastics, extruded
     RL: USES (Uses)
        (silane-crosslinked ethylene polymers contg. carbon, for covering of
        cables)
IT
     Alkenes, polymers
     RL: USES (Uses)
        (.alpha.-, polymers, with ethylene, linear low-d., silane-crosslinked,
        for semiconductive sheathing for cables)
ΙT
     74-85-1D, Ethylene, polymers with .alpha.-olefins and
     vinyltrimethoxysilane
                            2768-02-7D, Vinyltrimethoxysilane, polymers with
     polyolefins
                  9010-77-9D, Acrylic acid-ethylene copolymer, polymers with
     polyolefins and vinyltrimethoxysilane 9010-79-1D, Ethylene-propylene
     copolymer, polymers with polyolefins and vinyltrimethoxysilane
     9010-86-0D, Ethyl acrylate-ethylene copolymer, polymers with polyolefins
     and vinyltrimethoxysilane 24937-78-8D, Ethylene-vinyl acetate copolymer,
     polymers with polyolefins and vinyltrimethoxysilane
                                                         25103-74-6D,
     Ethylene-methyl acrylate copolymer, polymers with polyolefins and
     vinyltrimethoxysilane
     RL: USES (Uses)
        (crosslinked, contg. carbon, for semiconductive covering of cables)
IT
    7440-44-0, Carbon, properties
    RL: PRP (Properties)
        (elec. conductive, silane-crosslinked ethylene polymers contq., for
        semiconductive coverings of cables)
IT
    107240-66-4, Ethylene-propylene-vinyltrimethoxysilane graft copolymer
     113408-96-1, Ethyl acrylate-ethylene-vinyltrimethoxysilane graft copolymer
     RL: USES (Uses)
        (linear low-d., silane-crosslinked, for semiconductive covering of
```

cables)

```
ANSWER 1 OF 1 CAPLUS COPYRIGHT 2002 ACS
L1
     1993:104471 CAPLUS
AN.
DN
     118:104471
     Silane-crosslinked resin semiconductive compositions for cable covering
TI
    Nishiyama, Hidemi; Kimura, Hitoshi
IN
     Furukawa Electric Co., Ltd., Japan
PA
SO
     Jpn. Kokai Tokkyo Koho, 11 pp.
     CODEN: JKXXAF
DT
     Patent
     Japanese
LA
     ICM C08L023-08
IC
     ICS C08K003-04; C08K005-14; C08K005-54; C08K005-56; H01B001-24
     38-3 (Plastics Fabrication and Uses)
CC
     Section cross-reference(s): 76
FAN.CNT 1
                    KIND DATE
                                         APPLICATION NO. DATE
     PAŤENT NO.
     _____
                                          ______
                                          JP 1991-60448
                      A2
                           19921019
                                                          19910325 <--
     JP 04293945
PΙ
     The title compns comprise ethylene (I) polymers 60-95, .gtoreq.1 I
AΒ
     copolymers with vinyl acetate, propylene, Et acrylate (II), Me acrylate,
     and/or acrylic acid 5-40, elec. conductive carbon 15-80, org. silanes
     0.5-10.0, org. peroxides 0.05-5.0, and silanol condensation catalysts
     0.01-3.0 parts. Thus, a 5.7-mm-diam. twisted wire was covered with a
     compn. contg. LLDPE 80, I-II copolymer 20, elec. conductive carbon 60,
     vinyltrimethoxysilane 2.0, dicumyl peroxide 0.2, dibutyltin dilaurate 0.1,
     and Irganox 1010 0.3 part and crosslinked in water at 80.degree. for 24 h \,
     to form a 1.0-mm semiconductive layer showing elongation 350% and good
     surface smoothness.
     silane crosslinking ethylene polymer semiconductor
ST
     Semiconductor materials
TT
     Plastics, extruded
     RL: USES (Uses)
        (silane-crosslinked ethylene polymers contg. carbon, for covering of
        cables)
     Alkenes, polymers RL: USES (Uses)
IT
        (.alpha.-, polymers, with ethylene, linear low-d., silane-crosslinked,
        for semiconductive sheathing for cables)
     74-85-1D, Ethylene, polymers with .alpha.-olefins and
IT
     vinyltrimethoxysilane 2768-02-7D, Vinyltrimethoxysilane, polymers with
                  9010-77-9D, Acrylic acid-ethylene copolymer, polymers with
     polyolefins
                                           9010-79-1D, Ethylene-propylene
     polyolefins and vinyltrimethoxysilane
     copolymer, polymers with polyolefins and vinyltrimethoxysilane
     9010-86-0D, Ethyl acrylate-ethylene copolymer, polymers with polyolefins
     and vinyltrimethoxysilane 24937-78-8D, Ethylene-vinyl acetate copolymer,
     polymers with polyolefins and vinyltrimethoxysilane 25103-74-6D,
     Ethylene-methyl acrylate copolymer, polymers with polyolefins and
     vinyltrimethoxysilanë
     RL: USES (Uses)
        (crosslinked, contg. carbon, for semiconductive covering of cables)
     7440-44-0, Carbon, properties
IT
     RL: PRP (Properties)
        (elec. conductive, silane-crosslinked ethylene polymers contg., for
        semiconductive coverings of cables)
     107240-66-4, Ethylene-propylene-vinyltrimethoxysilane graft copolymer
IT
     113408-96-1, Ethyl acrylate-ethylene-vinyltrimethoxysilane graft copolymer
     RL: USES (Uses)
        (linear low-d., silane-crosslinked, for semiconductive covering of
        cables)
```

## WEST

#### **End of Result Set**

Generate Collection

L1: Entry 1 of 1

File: DWPI

Oct 22, 1998

DERWENT-ACC-NO: 1992-394623

DERWENT-WEEK: 199847

COPYRIGHT 2002 DERWENT INFORMATION LTD

TITLE: Silane-crosslinked semiconducting resin compsn. for power cable covering - is prepd. by mixing and kneading mixt. contg. polyethylene, ethylene@! copolymers, organo:silane cpd.

PATENT-ASSIGNEE:

ASSIGNEE

CODE

FURUKAWA ELECTRIC CO LTD

FURU

PRIORITY-DATA: 1991JP-0060448 (March 25, 1991)

PATENT-FAMILY:

PUB-NO

PUB-DATE

LANGUAGE

PAGES MAIN-IPC

JP 2813487 B2

October 22, 1998

010

C08F053\08

JP 04293945 A

October 19, 1992

011

C08L023/08

APPLICATION-DATA:

PUR - NO

APPL-DATE

APPL-NO

DESCRIPTOR

JP 2813487B2

March 25, 1991

1991JP-0060448

Previous Publ.

JP 2813487B2 JP04293945A

March 25, 1991

1991JP-0060448

JP 4293945

INT-CL (IPC): C08K 3/04; C08K 5/14; C08K 5/54; C08K 5/56; C08L 23/08; H01B 1/24

ABSTRACTED-PUB-NO: JP04293945A

BASIC-ABSTRACT:

The compsn. is characterised in that it is prepd. by mixing and kneading an intimate mixt. comprising 60-95 pts. wt. of a polyethylene, 5-40 pts. wt. of one or more ethylene copolymers selected from EVA copolymer, ethylene-propylene copolymer, ethylene-ethyl acrylate copolymer and ethylene-methyl acrylate copolymer, 15-80 pts. wt. of an electricoconductive carbon black and an organosilane cpd. with 0.05-5.0 pts. wt. of an organic peroxide and 0.01-3.0 pts. wt. of a silanol condensation catalyst.

The polyethylene is pref. e.g. a linear low density polyethylene (L-LDPE). The organosilane cpd. is, e.g. vinyl trimethoxysilane. The pref. organic peroxide is, e.g. dicumyl peroxide. The silanol condensation catalyst is, e.g. dibutyltin dilaurate.

USE/ADVANTAGE - Used as a semiconducting layer of power cable covering. It does not form any voids at the interface with outer insulating layer and gives good insulation characteristicref

CHOSEN-DRAWING: Dwg.0/5

TITLE-TERMS: SILANE CROSSLINK SEMICONDUCTOR RESIN COMPOSITION POWER CABLE COVER

PREPARATION MIX KNEAD MIXTURE CONTAIN POLYETHYLENE POLYETHYLENE@ COPOLYMER ORGANO SILANE COMPOUND DERWENT-CLASS: A17 A85 E19 L03 CPI-CODES: A04-G01E; A07-A02; A08-C05; A08-M01D; A08-R03; A09-A03; A11-A03; A12-E02A; E05-E02D; E05-F01; E10-A04B; E31-N04D; L03-A01B1; L03-A02E; CHEMICAL-CODES: Chemical Indexing M3 \*01\* Fragmentation Code C106 C810 M411 M782 M903 M904 M910 Q130 Q454 O610 Specfic Compounds 05085M Registry Numbers 92407 Chemical Indexing M3 \*02\* Fragmentation Code B414 B713 B720 B741 B831 H7 H713 H721 M210 M211 M212 M250 M272 M281 M283 M320 M411 M510 M520 M530 M540 M782 M903 M904 Q121 Q130 Q454 Q610 R043 Markush Compounds 199248-C6901-M Registry Numbers 92407 Chemical Indexing M3 \*03\* Fragmentation Code G010 G019 G100 K0 К9 K930 M280 M313 M322 M331 M340 M342 M373 M392 M414 M510 M520 M532 M540 M782 M903 M904 M910 Q130 Q454 Q610 R043 Specfic Compounds 00476M Registry Numbers 92407 Chemical Indexing M3 \*04\* Fragmentation Code A350 A923 A960 J0 J011 J1 J171 M210 M214 M225 M231 M250 M262 M281 M282 M320 M411 M510 M520 M530 M540 M620 M630 M650 M782 M903 M904 M910 Q121 Q130 Q454 Q610 R043 Specfic Compounds 00415M Registry Numbers 92407

UNLINKED-DERWENT-REGISTRY-NUMBERS: 0415U; 0476U; 1669U; 5085U; 5402U

### POLYMER-MULTIPUNCH-CODES-AND-KEY-SERIALS:

Key Serials: 0032 0037 0150 0205 0218 0219 0224 0226 0231 0239 0241 0242 0250 0495 0537 0544 0789 1058 2020 2217 2291 2292 2300 2302 2330 2551 2653 2727 3006 3020 3151 3153 3155 3158 3319

Multipunch Codes: 014 02& 034 04- 040 041 046 047 050 066 067 074 075 076 08& 081 082 083 116 15- 17& 229 231 266 27& 28& 292 299 307 308 310 341 392 41- 44& 444 473 477 48-506 509 531 54& 575 58& 595 688 690 720 723

5

SECONDARY-ACC-NO:
CPI Secondary Accession Numbers: C1992-175161